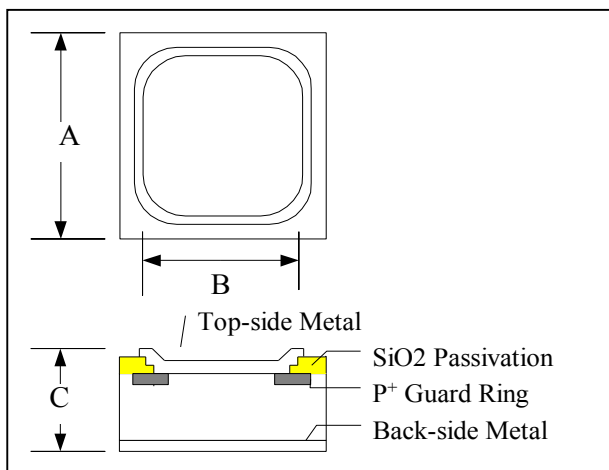


ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	UNIT
Reverse Breakdown Voltage: Ir=0.20mA	VBRM	50	Volt
Average Rectified Forward Current	IFAV	15.0	Amp
Maximum Instantaneous Forward Voltage			
@ 10 Amperes, Ta=25°C		0.480	
@ 15 Amperes, Ta=25°C	VF MAX	0.530	Volt
Maximum Instantaneous Reverse Current			
VR= 53 Volt, Ta=25°C	IR MAX	50	uA
MAXIMUM RATINGS			
Nonrepetitive Peak Surge Current			
Semi-Sine Wave, Duty = 8.3ms · 1cycle	IFSM	80	Amp
Operating Junction Temperature	Tj	150	°C
Storage Temperatures	TSTG	-50 to +150	°C

1. Specification is applied to die only. Actual performance may degrade when assembled. BW does not guarantee device performance after assembly.
2. Suggest to storage in Nitrogen cabinet, 45-60% RH, 22-26 °C for 6 months.
3. Data sheet information is subjected to change without notice.
4. Suggest Soldering profile (Pb92.5%,5%Sn,Ag2.5%): Soldering peak Temp. 340~350 °C 3~5min.

DICE OUTLINE DRAWING



DIM	ITEM	μ m	Mil
A	Die Size	1397	55.00
B	Top Metal Pad Size	1197	47.13
C	Thickness	280	11.00

(1)Cutting street width is around 60μm.
 (2)Both of top-side and back-side metals are Ti/Ni/Ag.
 (3) Top-side Ti/Ni thk: 0.42um, Ag thk: 3.5um
 (4) Thickness(C) tolerance: +/-10um